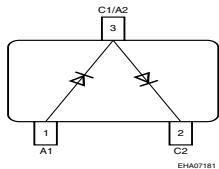
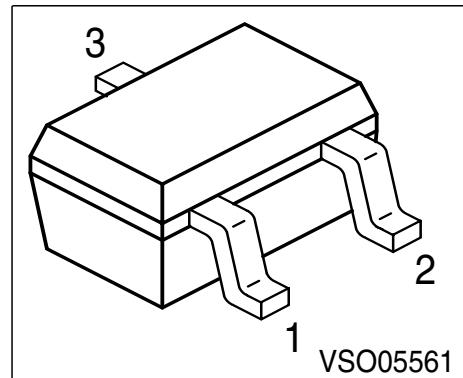


## Silicon Schottky Diode

### Preliminary data

- DBS mixer applications up to 12 GHz
- Low noise figure
- Low barrier type



**ESD:** Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration			Package
BAT 15-04W	S8s	1 = A1	2=C2	3=C1/A2	SOT-323

### Maximum Ratings

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	4	V
Forward current	$I_F$	110	mA
Total power dissipation, $T_S \leq tbd$ °C	$P_{tot}$	100	mW
Junction temperature	$T_j$	150	°C
Operating temperature range	$T_{op}$	-55 ... 150	°C
Storage temperature	$T_{stg}$	-55 ... 150	°C

### Thermal Resistance

Junction - ambient 1)	$R_{thJA}$	$\leq tbd$	K/W
Junction - soldering point	$R_{thJS}$	$\leq tbd$	

1) Package mounted on alumina 15mm x 17.6mm x 0.7mm)

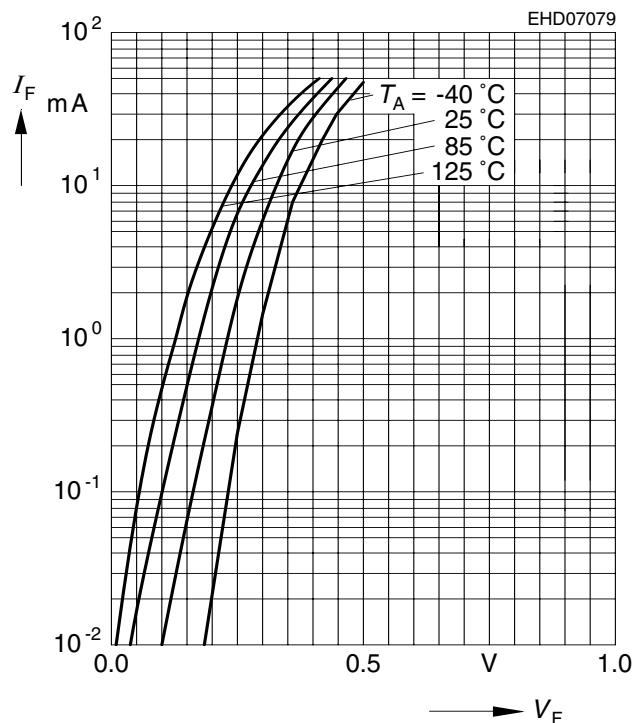
**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

<b>Parameter</b>	<b>Symbol</b>	<b>Values</b>			<b>Unit</b>
		<b>min.</b>	<b>typ.</b>	<b>max.</b>	
<b>DC characteristics</b>					
Breakdown voltage $I_{(BR)} = 5 \mu\text{A}$	$V_{(\text{BR})}$	4	-	-	V
Forward voltage $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$	$V_F$	-	0.23	0.32	
Forward voltage matching <sup>1)</sup> $I_F = 10 \text{ mA}$	$\Delta V_F$	-	-	20	mV
<b>AC characteristics</b>					
Diode capacitance $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	$C_T$	-	-	0.35	pF
Forward resistance $I_F = 10\text{mA} / 50\text{mA}$	$R_F$	-	5.5	-	$\Omega$

1)  $\Delta V_F$  is difference between lowest and highest  $V_F$  in component

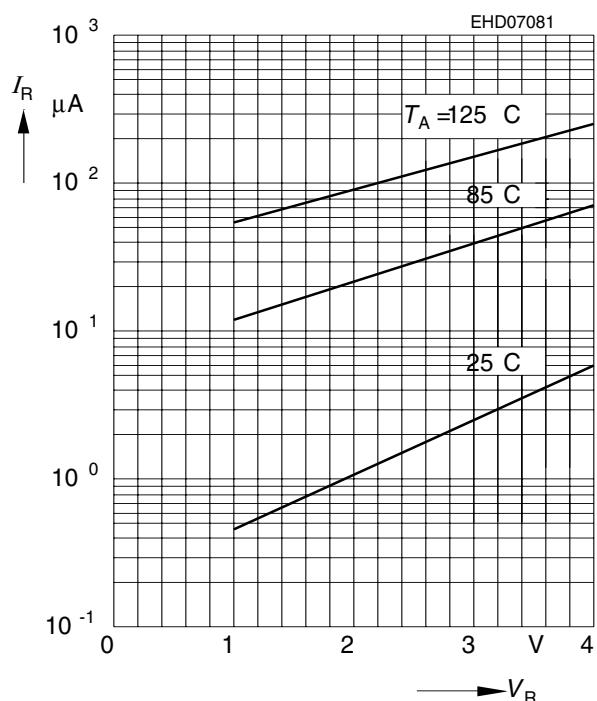
**Forward current  $I_F = f(V_F)$**

$T_A$  = Parameter



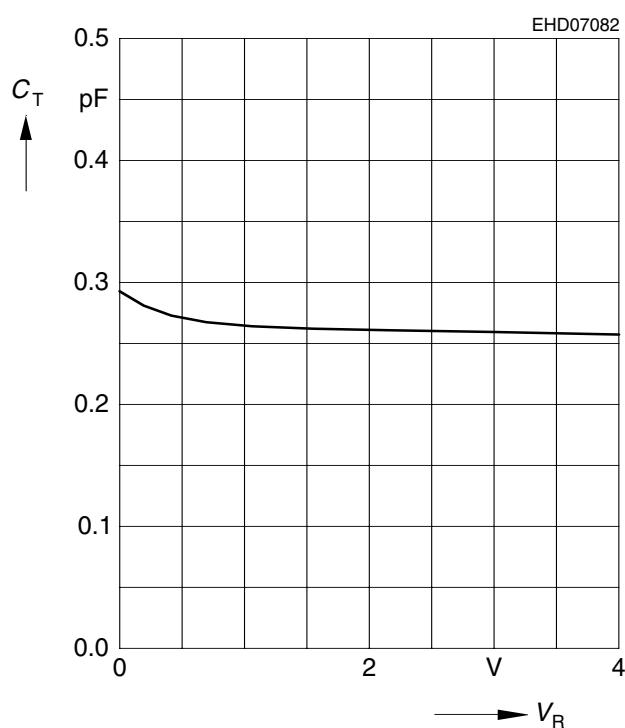
**Reverse current  $I_R = f(V_R)$**

$T_A$  = Parameter



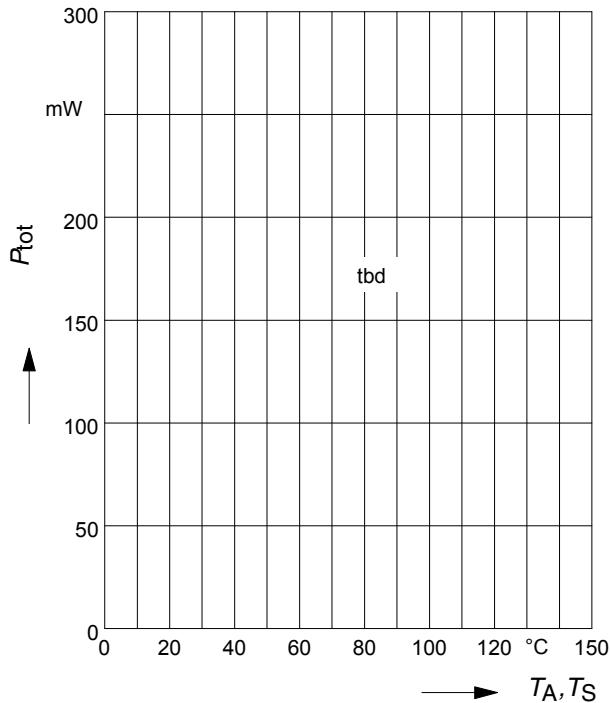
**Diode capacitance  $C_T = f(V_R)$**

$f = 1\text{MHz}$

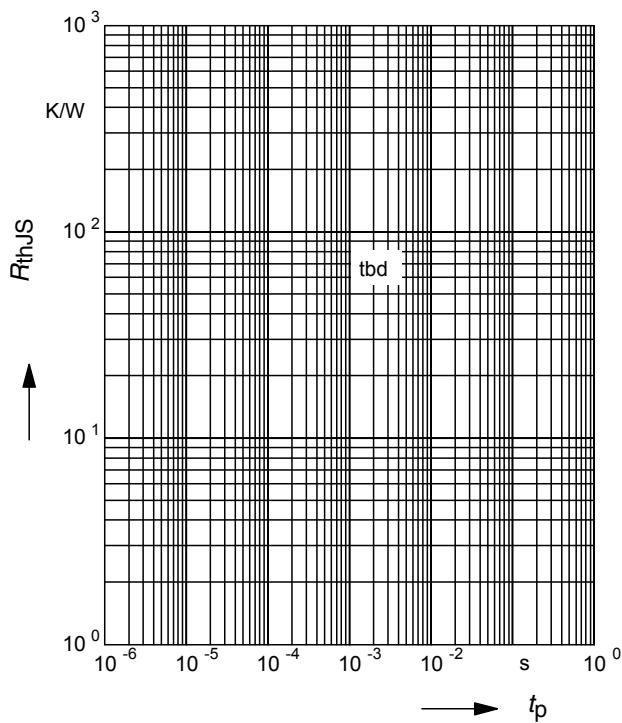


**Forward current  $I_F = f(T_A^*; T_S)$**

\* Package mounted on epoxy



**Permissible Pulse Load  $R_{thJS} = f(t_p)$**



**Permissible Pulse Load**

$I_{Fmax} / I_{FDC} = f(t_p)$

